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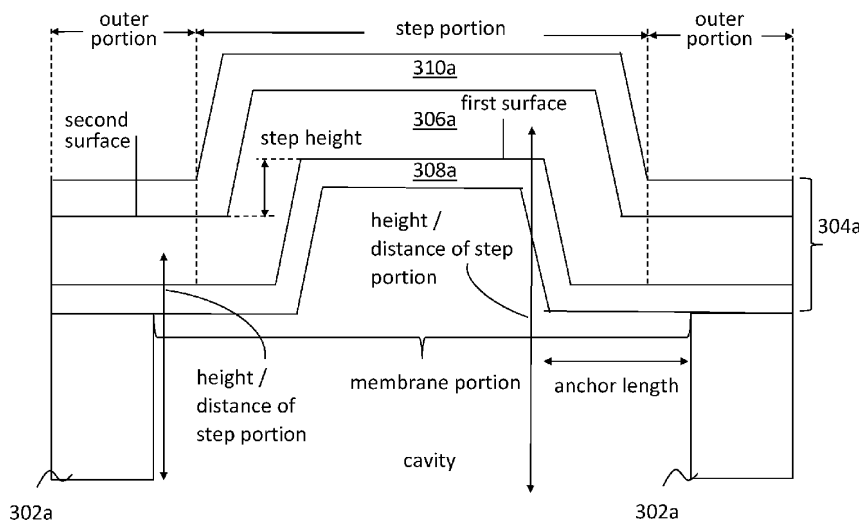
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(54) Title: PIEZOELECTRIC DEVICE AND METHOD OF FORMING THE SAME

FIG. 3A



(57) Abstract: Various embodiments may relate to a piezoelectric device including a substrate at least partially defining a cavity, a piezoelectric stacked arrangement with a step portion over the cavity and an outer portion adjoining the step portion, a continuous piezoelectric layer, and a continuous first electrode layer in contact with a first surface of the piezoelectric layer. The first electrode layer may extend between at least a part of the outer portion of the piezoelectric stacked arrangement and at least a part of the step portion of the piezoelectric stacked arrangement. The piezoelectric stacked arrangement may further include a continuous second electrode layer in contact with a second surface of the piezoelectric layer. The second electrode layer may extend between at least a part of the outer portion of the piezoelectric stacked arrangement and at least a part of the step portion of the piezoelectric stacked arrangement.

[Continued on next page]

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